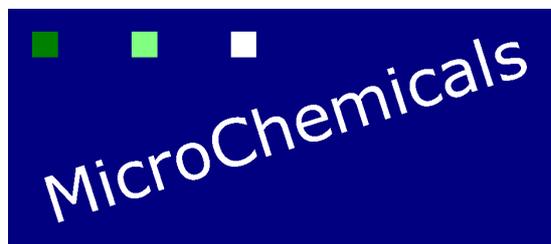


TI PRIME

adhesion promoter

Technical Data Sheet
revised 12/2002



MicroChemicals GmbH
Schillerstrasse 18
D-89077 Ulm

Fon +49 (0) 731 36080409
Mobil +49 (0) 177 3332453
Fax +49 (0) 731 1517024
Email info@MicroChemicals.com
Internet www.microchemicals.com

General Information

The TI PRIME adhesion promoter improves resist adhesion on substrates like Si or glass



Processing the TI PRIME

(in chronological order)

- **Substrate preparation:** After (optional, but recommended) cleaning the substrate with acetone and subsequently isopropyle, put the substrate on the hotplate at a minimum temperature of 120 °C for 10 minutes to remove adsorbed water from the substrates surface. Alternatively, you can use a furnace at same temperature for 30 min.
- **Spin coat the TI PRIME** at approx. 2000-4000 U/min for approx. 20 seconds. After spin-coating, no residual drops or film of TI PRIME should be visible.
- **Bake the substrate** at 120°C for 2 minutes on the hotplate (when using a furnace, 130°C for 10 min is recommended)
- **Proceed with spin-coating the resist immediately and proceed as usual.**

Note: TI Prime contains Titanium. For CMOS processes use (eg. RCA-) cleaning procedure of the substrates after lithography before you apply high-temperatures.